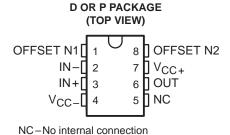
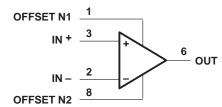
SLOS099B - OCTOBER 1983 - REVISED AUGUST 1996

- **Low Noise**
- No External Components Required
- Replaces Chopper Amplifiers at a Lower Cost
- **Single-Chip Monolithic Fabrication**
- Wide Input Voltage Range 0 to  $\pm$ 14 V Typ
- Wide Supply Voltage Range  $\pm 3$  V to  $\pm 18$  V
- Essentially Equivalent to Fairchild µA714 **Operational Amplifiers**
- Direct Replacement for PMI OP07C and OP07D



### symbol



## description

These devices represent a breakthrough in operational amplifier performance. Low offset and long-term stability are achieved by means of a low-noise, chopperless, bipolar-input-transistor amplifier circuit. For most applications, external components are not required for offset nulling and frequency compensation. The true differential input, with a wide input voltage range and outstanding common-mode rejection, provides maximum flexibility and performance in high-noise environments and in noninverting applications. Low bias currents and extremely high input impedances are maintained over the entire temperature range. The OP07 is unsurpassed for low-noise, high-accuracy amplification of very low-level signals.

These devices are characterized for operation from 0°C to 70°C.

### **AVAILABLE OPTIONS**

	TA VIOMAX AT 25°C SMALL OUTLINE (D) (P)		PACKAGED DEVICES			
TA				CHIP FORM (Y)		
0°C to 70°C	150 μV	OP07CD OP07DD	OP07CP OP07DP	OP07Y		

The D package is available taped and reeled. Add the suffix R to the device type (e.g., OP07CDR). The chip form is tested at  $T_A = 25$ °C.



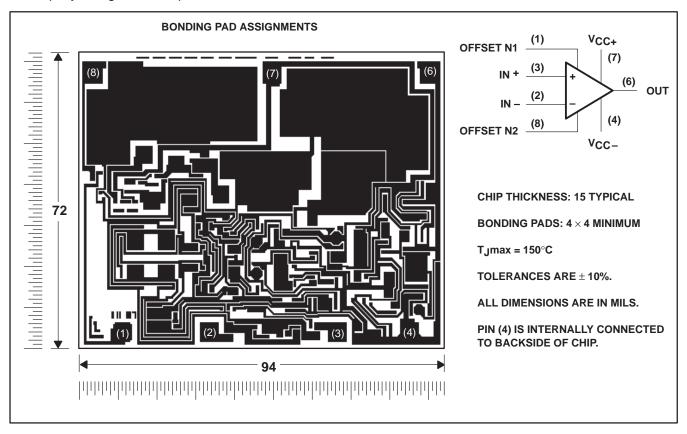
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



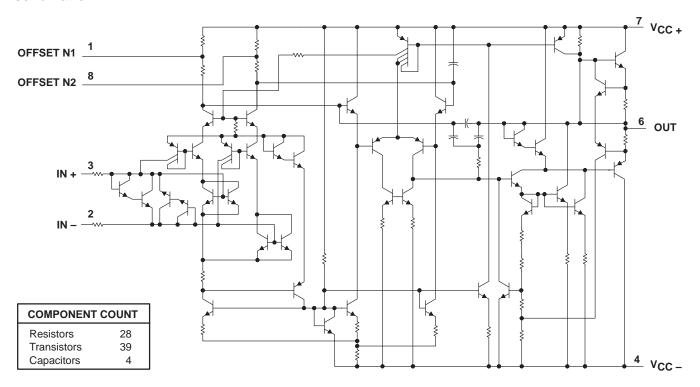
SLOS099B - OCTOBER 1983 - REVISED AUGUST 1996

### **OP07Y** chip information

These chips, properly assembled, display characteristics similar to the OP07. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



### schematic



## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC+</sub> (see Note 1)	22 V
Supply voltage, V <sub>CC</sub>	22 V
Differential input voltage (see Note 2)	$\dots \dots \pm 30 \; V$
Input voltage, V <sub>I</sub> (either input, see Note 3)	±22 V
Duration of output short circuit (see Note 4)	unlimited
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 5)	500 mW
Operating free-air temperature range, T <sub>A</sub>	0°C to 70°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

- NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between  $V_{CC+}$  and  $V_{CC-}$ .
  - 2. Differential voltages are at IN+ with respect to IN-.
  - 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
  - 4. The output may be shorted to ground or either power supply.
  - 5. For operation above 64°C free-air temperature, derate the D package to 464 mW at 70°C at the rate of 5.8 mW/°C.

### recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V <sub>CC±</sub>		±3	±18	V
Common-mode input voltage, V <sub>IC</sub>	V <sub>CC±</sub> = ±15 V	-13	13	V
Operating free-air temperature, TA	0	70	°C	



# TEXAS INSTRUMENTS OST OFFICE BOX 655303\* DALLAS, TEXAS 7.

## electrical characteristics at specified free-air temperature, $V_{CC} \pm = \pm 15 \text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS†		т.		OP07C		OP07D			UNIT
		I EST CON	ADITIONS	TA	MIN	TYP	MAX	MIN	TYP	MAX	UNII
VIO	Input offset voltage	V <sub>O</sub> = 0,	R <sub>S</sub> = 50 Ω	25°C		60	150		60	150	μV
VIO	input onset voitage	VO = 0,	VO = 0, $VS = 30.22$	0°C to 70°C		85	250		85	250	μν
ανιο	Temperature coefficient of input offset voltage	$V_{O} = 0$ ,	$R_S = 50 \Omega$	0°C to 70°C		0.5	1.8		0.7	2.5	μV/°C
	Long-term drift of input offset voltage	See Note 6				0.4			0.5		μV/mo
	Offset adjustment range	$R_S = 20 \text{ k}\Omega$ ,	See Figure 1	25°C		±4			±4		mV
lio	Input offset current			25°C		8.0	6		0.8	6	nA
liO	input onset current			0°C to 70°C		1.6	8		1.6	8	
αΙΙΟ	Temperature coefficient of input offset current			0°C to 70°C		12	50		12	50	pA/°C
lin.	Input bias current			25°C		±1.8	±7		±2	±12	nA
ΙΒ	input bias current			0°C to 70°C		±2.2	±9		±3	±14	IIA
αIIB	Temperature coefficient of input bias current			0°C to 70°C		18	50		18	50	pA/°C
V/10.5	Common-mode input voltge range			25°C	±13	±14		±13	±14		V
VICR				0°C to 70°C	±13	±13.5		±13	±13.5		
	Peak output voltage	$R_L \ge 10 \text{ k}\Omega$			±12	±13		±12	±13		
Vou		$R_L \ge 2 \ k\Omega$		25°C	±11.5	±12.8		±11.5	±12.8		V
VОМ		$R_L \ge 1 \ k\Omega$		]		±12			±12		
		$R_L \ge 2 \ k\Omega$		0°C to 70°C	±11	±12.6		±11	±12.6		
		$V_{CC\pm} = \pm 3 \text{ V},$ $R_L \ge 500 \text{ k}\Omega$	$V_0 = \pm 0.5 V$ ,	25°C	100	400			400		
AVD	Large-signal differential voltage amplification	Vo - +10 V	$R_1 = 2 k\Omega$	25°C	120	400		120	400		V/mV
		$V_0 = \pm 10 \text{ V},$	K[ = 2 K22	0°C to 70°C	100	400		100	400		
B <sub>1</sub>	Unity-gain bandwidth			25°C	0.4	0.6		0.4	0.6		MHz
rį	Input resistance			25°C	8	33		7	31		МΩ
CMRR	Common mode rejection ratio	V:- 142 V	Do 50.0	25°C	100	120		94	110		4D
CIVIKK	Common-mode rejection ratio	$V_{IC} = \pm 13 \text{ V},$	$R_S = 50 \Omega$	0°C to 70°C	97	120		94	106		dB
	Complex soltone and soliticity (AV) = (AV) = -	$V_{CC\pm} = \pm 3 \text{ V to}$	o ±18 V,	25°C		7	32		7	32	\/\/
ksvs	Supply voltage sensitivity ( $\Delta V_{IO}/\Delta V_{CC}$ )	$R_S = 50 \Omega$	•	0°C to 70°C		10	51		10	51	μV/V
		$V_{O} = 0$ ,	No load			80	150		80	150	
PD	Power dissipation	$V_{CC\pm} = \pm 3 \text{ V},$ No load	V <sub>O</sub> = 0,	25°C		4	8		4	8	mW

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the averaged trend line of drift versus time over extended periods after the first thirty days of operation.

# operating characteristics, $V_{CC\pm}$ = $\pm 15$ V, $T_A$ = $25^{\circ}C$

	PARAMETER	TEST	OP07C			OP07D			UNIT								
FARAWETER		CONDITIONST	MIN	TYP	MAX	MIN	TYP	MAX	UNIT								
	Equivalent input noise voltage	f = 10 Hz		10.5			10.5										
$V_n$		f = 100 Hz		10.2			10.3		nV/√ <del>Hz</del>								
		f = 1 kHz		9.8			9.8										
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38			0.38		μV								
	Equivalent input noise current	f = 10 Hz		0.35			0.35		pA/√ <del>Hz</del>								
In		f = 100 Hz		0.15			0.15										
		f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz	f = 1 kHz		0.13			0.13	
I <sub>N(PP)</sub>	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15			15		pА								
SR	Slew rate	$R_L \ge 2 k\Omega$		0.3			0.3		V/μs								

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

# electrical characteristics, $V_{CC\pm}$ = $\pm 15$ V, $T_A$ = 25°C (unless otherwise noted)

DADAMETED		TEST SOMBITIONS!			OP07Y			LINUT
	PARAMETER	TEST CONDITIONS†			MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$R_S = 50 \Omega$				60	150	μV
	Long-term drift of input offset voltage	See Note 6				0.5		μV/mo
	Offset adjustment range	$R_S = 20 \text{ k}\Omega$ ,	See Figure 1			±4		mV
I <sub>IO</sub>	Input offset current					0.8	6	nA
I <sub>IB</sub>	Input bias current					±2	±12	nA
VICR	Common-mode input voltage range				±13	±14		V
		R <sub>L</sub> ≤ 10 kΩ			±12	±13		
VOM	Peak output voltage	$R_L \le 2 k\Omega$			±11.5	±12.8		V
		R <sub>L</sub> ≤ 1 kΩ				±12		
Δ	Large-signal differential voltage amplification	$V_{CC\pm} = \pm 3 \text{ V},$	$V_0 = \pm 0.5 V$ ,	R <sub>L</sub> ≤ 500 kΩ		400		
AVD		$V_0 = \pm 10 \text{ V},$	R <sub>L</sub> = 2 kΩ		120	400		
B <sub>1</sub>	Unity-gain bandwidth				0.4	0.6		MHz
rį	Input resistance				7	31		MΩ
CMRR	Common-mode input resistance	$V_{IC} = \pm 13 \text{ V},$	R <sub>S</sub> = 50 Ω		94	110		dB
ksvs	Supply-voltage rejection ratio (ΔV <sub>CC</sub> /ΔV <sub>IO</sub> )	$V_{CC\pm} = \pm 3 \text{ V to}$	o ±18 V,	$R_S = 50 \Omega$		7	32	μV/V
D-	Power dissipation	$V_{O} = 0,$	No load			80	150	MΩ
PD		$V_{CC\pm} = \pm 3 \text{ V},$	V <sub>O</sub> = 0,	No load		4	8	10122

NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the averaged trend line of drift versus time over extended periods after the first thirty days of operation.

SLOS099B - OCTOBER 1983 - REVISED AUGUST 1996

# operating characteristics, $V_{CC\pm}$ = $\pm 15$ V, $T_A$ = $25^{\circ}C$

PARAMETER		TEST CONDITIONS†	OP07Y			UNIT	
		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
	Equivalent input noise voltage	f = 10 Hz		10.5		nV/√Hz	
Vn		f = 1 kHz		10.3			
		f = 0.1 Hz to 10 Hz		9.8			
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38		μV	
	Equivalent input noise current	f = 10 Hz		0.35			
In		f = 100 Hz		0.15		pA/√ <del>Hz</del>	
		f = 1 kHz		0.13			
I <sub>N(PP)</sub>	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15		pА	
SR	Slew rate	$R_L = 2 k\Omega$		0.3		V/μs	

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

### **APPLICATION INFORMATION**

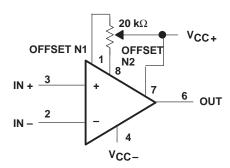


Figure 1. Input Offset Voltage Null Circuit

#### **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated